SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

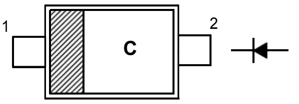
for low current rectification and high speed switching applications

Features

- Extremely small surface mounting type

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



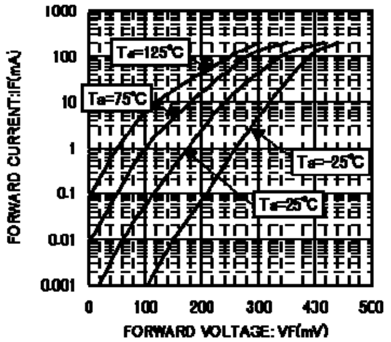
Top View
Marking Code: "**C**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

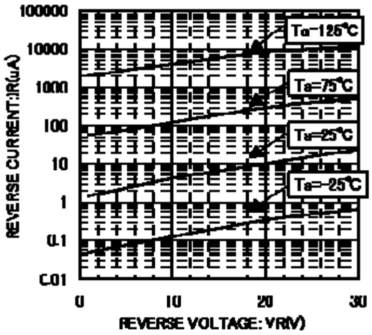
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

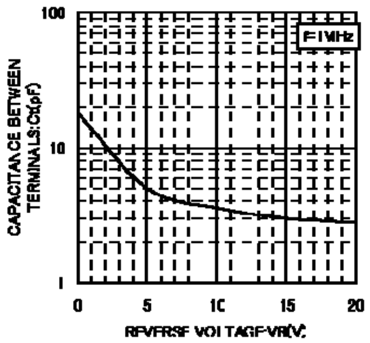
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 10 mA I_F = 200 mA	V_F	0.35 0.5	V
Reverse Current at V_R = 10 V	I_R	30	µA



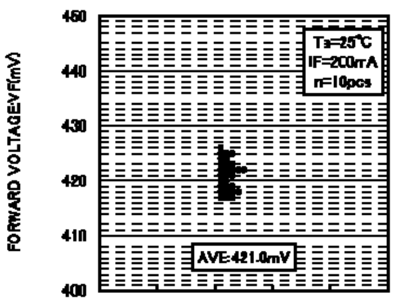
VF–IF CHARACTERISTICS



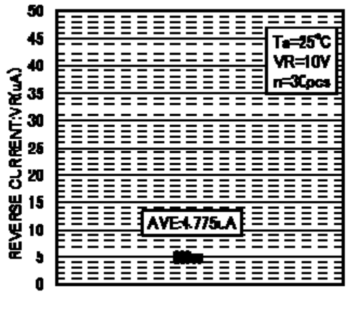
VR–IR CHARACTERISTICS



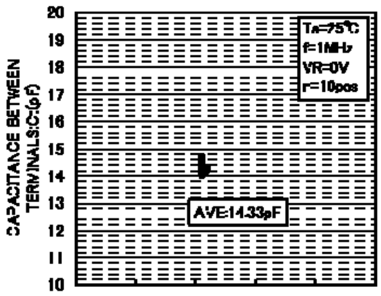
VR–Ct CHARACTERISTICS



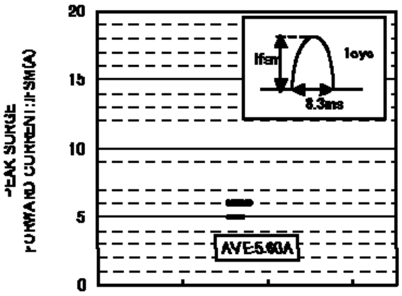
VF DISPERSION MAP



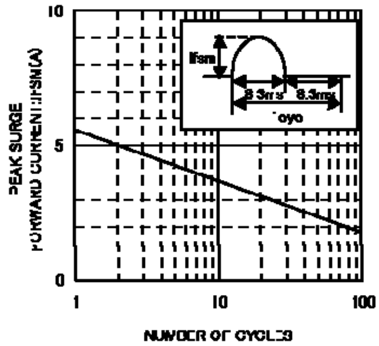
IR DISPERSION MAP



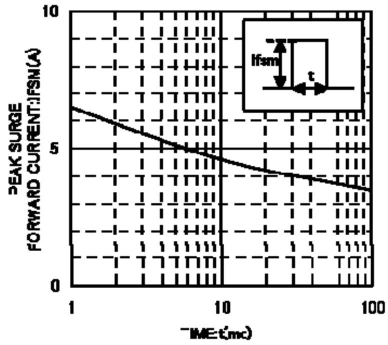
Ct DISPERSION MAP



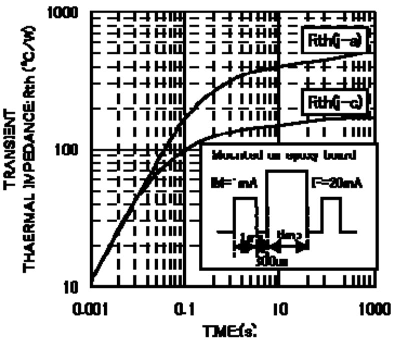
IFSM DISPERSION MAP



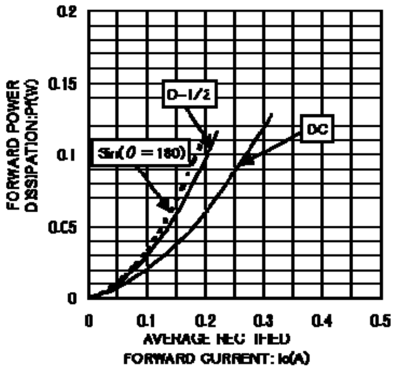
IFSM–CYCLE CHARACTERISTICS



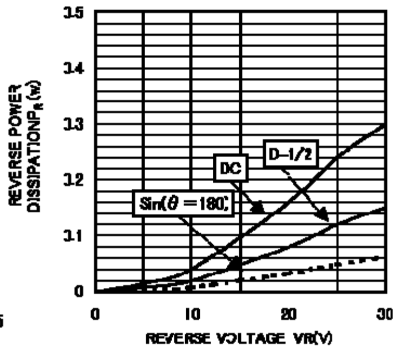
IFSM–t CHARACTERISTICS



Rth–t CHARACTERISTICS



Io–Pf CHARACTERISTICS



VR–P_R CHARACTERISTICS